

High Speed, Precision JFET Input Operational Amplifier

FEATURES

- Guaranteed Slew Rate: 23V/µs Min Guaranteed Offset Voltage: 250µV Max
 - -55°C to 125°C: 750μV Max
- Guaranteed Drift: 5µV/°C Max **Guaranteed** Bias Current: 70°C. 180pA Max
 - 125°C, 4nA Max
- Gain-Bandwidth Product: 8.5MHz Typ
- Settling Time to 0.05% (10V Step): 0.9µs Typ

APPLICATIONS

- Fast D/A Output Amplifiers (12, 14, 16 Bits)
- High Speed Instrumentation
- Fast, Precision Sample and Hold
- Voltage-to-Frequency Converters
- Logarithmic Amplifiers

DESCRIPTION

The LT®1022 JFET input operational amplifier combines high speed and precision performance.

A 26V/µs slew rate and 8.5MHz gain-bandwidth product are simultaneously achieved with offset voltage of typically 80µV, 1.5µV/°C drift, bias currents of 50pA at 70°C, 500pA at 125°C. The output delivers 20mA of load current without gain degradation.

The 250µV maximum offset voltage specification represents less than 1/2 least significant bit error in a 14-bit, 10V system.

The LT1022A meets or exceeds all OP-16A and OP-16E specifications. It is faster and more accurate without stability problems at cold temperatures.

The LT1022 can be used as the output amplifier for 12-bit current output D/A converters, as shown below.

For a more accurate, lower power dissipation, but slower JFET input op amp, please refer to the LT1055 data sheet.

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TYPICAL APPLICATION

CONVERTER (e.g., 6012, 565 OR DAC-80)

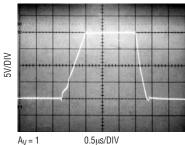
C_{F} 15V 0mA TO 2mA OUTPUT LT1022 0V TO 10V 12-BIT CURRENT OUTPUT D/A

12-Bit Voltage Output D/A Converter

 $C_F = 15pF TO 33pF$ SETTLING TIME TO 2mV (0.8 LSB) = 1.5µs TO 2µs

LT1022 • TA01

Large-Signal Response



C_L = 100pF $T_A = 25^{\circ}C$

 $V_S = \pm 15V$



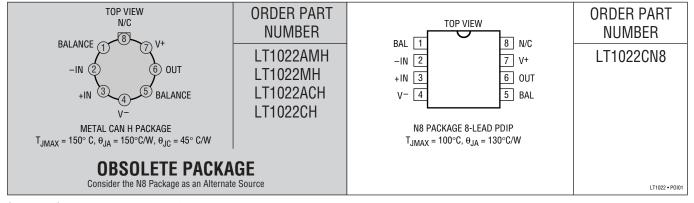
ABSOLUTE MAXIMUM RATINGS

(Note 1)

Supply Voltage	±20V
Differential Input Voltage	
Input Voltage	±20V
Output Short Circuit Duration	Indefinite

Operating Temperature Range	
LT1022AM/1022M (OBSOLETE)	55°C to 125°C
LT1022AC/1022C	0°C to 70°C
Storage Temperature Range	65°C to 150°C
Lead Temperature (Soldering, 10 sec.))300°C

PACKAGE/ORDER INFORMATION



Consult LTC Marketing for parts specified with wider operating temperature ranges.

ELECTRICAL CHARACTERISTICS $V_S = \pm 15 V$, $T_A = 25 ^{\circ} C$, $V_{CM} = 0 V$ unless otherwise noted.

			LT1022AM LT1022AC			LT10			
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
V _{OS}	Input Offset Voltage (Note 2)	H Package N8 Package		80	250		100 160	600 1000	μV μV
I _{OS}	Input Offset Current	Fully Warmed Up		2	10		2	20	pA
I _B	Input Bias Current	Fully Warmed Up V _{CM} = +10V		±10 30	±50 100		±10 30	±50 150	pA pA
	Input Resistance—Differential —Common Mode	V _{CM} = -11V to 8V V _{CM} = 8V to 11V		10 ¹² 10 ¹² 10 ¹¹			10 ¹² 10 ¹² 10 ¹¹		Ω Ω Ω
	Input Capacitance			4			4		pF
e _n	Input Noise Voltage	0.1Hz to 10Hz		2.5			2.8		μV/ _{P-P}
e _n	Input Noise Voltage Density	$f_0 = 10$ Hz (Note 3) $f_0 = 1$ kHz (Note 4)		28 14	50 20		30 15	60 22	nV/√ Hz nV/√ Hz
i _n	Input Noise Current Density	f ₀ = 10Hz, 1kHz (Note 5)		1.8	4		1.8	4	fA√Hz
A _{VOL}	Large Signal Voltage Gain	$V_0 = \pm 10V R_L = 2k$ $R_L = 1k$	150 130	400 300		120 100	400 300		V/mV V/mV
	Input Voltage Range		±10.5	±12		±10.5	±12		V
CMRR	Common-Mode Rejection Ratio	$V_{CM} = \pm 10.5V$	86	94		82	92		dB
PSRR	Power Supply Rejection Ratio	$V_S = \pm 10V \text{ to } \pm 18V$	88	104		86	102		dB
V _{OUT}	Output Voltage Swing	R _L = 2k	±12	±13.2		±12	±13.2		V
SR	Slew Rate		23	26		18	24		V/µs
									1022fa

ELECTRICAL CHARACTERISTICS

 $V_S = \pm 15V$, $T_A = 25^{\circ}C$, $V_{CM} = 0V$ unless otherwise noted.

			LT1022AM LT1022AC				22M, LT10 LT1022CN8		
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
GBW	Gain-Bandwidth Product	f = 1MHz		8.5			8.0		MHz
Is	Supply Current			5.2	7.0		5.2	7.0	mA
	Settling Time	A = +1 or A = -1 10V Step to 0.05% 10V Step to 0.02%		0.9 1.3			0.9 1.3		μ\$ μ\$
	Offset Voltage Adjustment Range	R _{POT} = 100k		±7			±7		mV

The ullet denotes the specifications which apply over the full operating temperature range of $V_{CM}=0V$, $0^{\circ}C \leq T_{A} \leq 70^{\circ}C$. $V_{S}=\pm 15V$, unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS		MIN	LT1022AC TYP	MAX	MIN	LT1022CH LT1022CN8 Typ		UNITS
V _{OS}	Input Offset Voltage (Note 2)	H Package N8 Package	•		140	480		180 300	1000 1700	μV μV
	Average Temperature Coefficient of Input Offset Voltage	H Package N8 Package (Note 6)	•		1.3	5.0		1.8 3.0	9.0 15.0	μV/°C μV/°C
I _{OS}	Input Offset Current	Warmed Up, T _A = 70°C	•		15	80		18	100	pA
I _B	Input Bias Current	Warmed Up, T _A = 70°C	•		±50	±200		±60	±250	pA
A _{VOL}	Large-Signal Voltage Gain	$V_0 = \pm 10V, R_L = 2k$	•	80	250		60	250		V/mV
CMRR	Common Mode Rejection Ratio	V _{CM} = ±10.4V	•	85	93		80	91		dB
PSRR	Power Supply Rejection Ratio	V _S = ±10V to ±18V	•	86	103		84	101		dB
V _{OUT}	Output Voltage Swing	R _L = 2k	•	±12	±13.1		±12	±13.1		V

The ullet denotes the specifications which apply over the full operating temperature range of $-55^{\circ}C \leq T_A \leq 125^{\circ}C$. $V_S = \pm 15V$, $V_{CM} = 0V$, unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS		MIN	LT1022AM TYP	MAX	MIN	LT1022M TYP	MAX	UNITS
V _{OS}	Input Offset Voltage	(Note 2)	•		230	750		300	1500	μV
	Average Temperature Coefficient of Input Offset Voltage	(Note 6)	•		1.5	5.0		2.0	9.0	μV/°C
I _{OS}	Input Offset Current	Warmed Up, T _A = 125°C	•		0.3	2.0		0.30	3.0	nA
I _B	Input Bias Current	Warmed Up, T _A = 125°C	•		± 0.5	± 4.0		± 0.7	± 6.0	nA
A _{VOL}	Large Signal Voltage Gain	$V_0 = \pm 10V, R_L = 2k$	•	40	120		35	120		V/mV
CMRR	Common-Mode Rejection Ratio	V _{CM} = ±10.4V	•	85	92		80	90		dB
PSRR	Power Supply Rejection Ratio	$V_S = \pm 10V \text{ to } \pm 17V$	•	86	102		84	100		dB
V _{OUT}	Output Voltage Swing	R _L = 2k	•	±12	±12.9		±12	±12.9		V

Note 1: Absolute Maximum Ratings are those values beyond which the life of a device may be impaired.

Note 2: Offset voltage is measured under two different conditions: (a) approximately 0.5 seconds after application of power; (b) at $T_A = 25^{\circ}C$, with the chip self-heated to approximately $45^{\circ}C$ to account for chip temperature rise when the device is fully warmed up.

Note 3: 10Hz noise voltage density is sample tested on every lot of A grades. Devices 100% tested at 10Hz are available on request.

Note 4: This parameter is tested on a sample basis only.

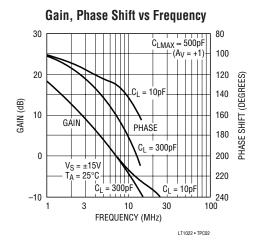
Note 5: Current noise is calculated from the formula: $i_n = (2ql_B)^{1/2}$, where $q = 1.6 \cdot 10^{-19}$ coulomb. The noise of source resistors up to $1G\Omega$ swamps the contribution of current noise.

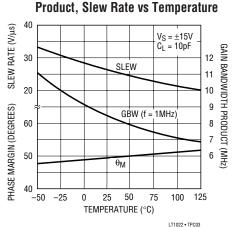
Note 6: Offset voltage drift with temperature is practically unchanged when the offset voltage is trimmed to zero with a 100k potentiometer between the balance terminals and the wiper tied to V^+ . Devices tested to tighter drift specifications are available on request.



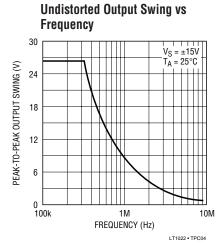
TYPICAL PERFORMANCE CHARACTERISTICS

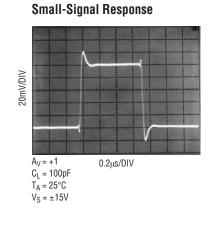
Gain vs Frequency 140 $V_S = \pm 15V$ 120 100 $T_{A} = 25^{\circ}C$ 80 GAIN (dB) 60 T_A = -55°C 40 125°C 20 0 100k 10 100 1k 10k 1M 10M 100M FREQUENCY (Hz) LT1022 • TPC01

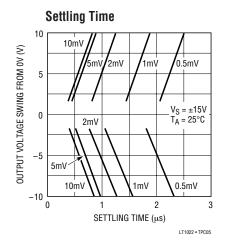




Phase Margin, Gain Bandwidth







The typical behavior of many LT1022 parameters is identical to the LT1056. Please refer to the LT1055/1056 data sheet for the following typical performance characteristics:

Input Bias and Offset Currents vs Temperature
Input Bias Current Over the Common-Mode Range
Distribution of Input Offset Voltage (H and N8 Package)
Distribution of Offset Voltage Drift with Temperature
Warm-Up Drift
Long Term Drift of Representative Units
0.1Hz to 10Hz Noise
Voltage Noise vs Frequency
Noise vs Chip Temperature

Short Circuit Current vs Time
Output Impedance vs Frequency
Common Mode Range vs Temperature
Common Mode and Power Supply Rejections vs Temperature
Common Mode Rejection Ratio vs Frequency
Power Supply Rejection Ratio vs Frequency
Voltage Gain vs Temperature
Supply Current vs Supply Voltage
Output Swing vs Load Resistance

TECHNOLOGY TECHNOLOGY

APPLICATIONS INFORMATION

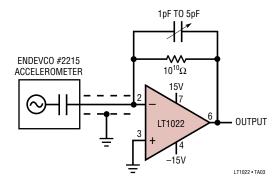
The LT1056 applications information is directly applicable to the LT1022. Please consult the LT1055/1056 data sheet for details on:

- (1) plug-in compatibility to industry standard devices
- (2) offset nulling
- (3) achieving picoampere/microvolt performance

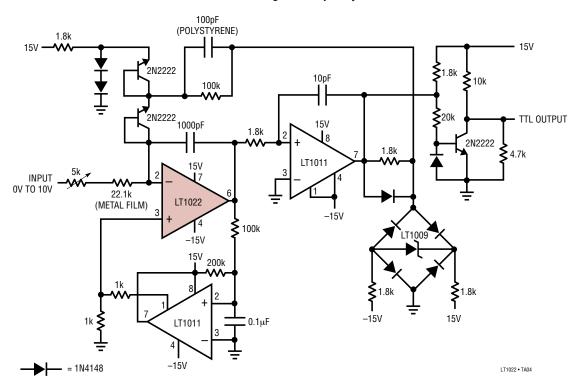
- (4) phase-reversal protection
- (5) high speed operation (including settling time test circuit)
- (6) noise performance
- (7) simplified circuit schematic

TYPICAL APPLICATIONS

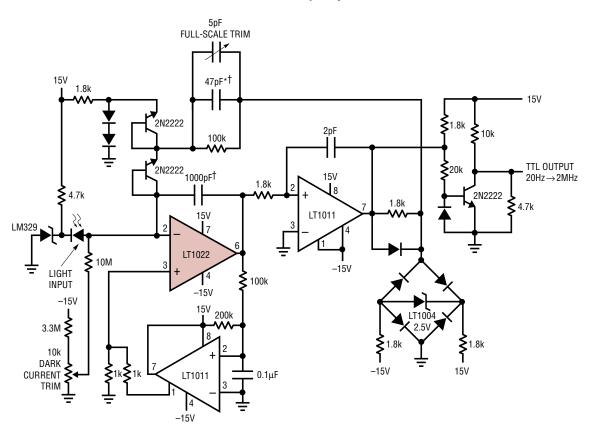
Fast Piezoelectric Accelerometer



10Hz to 1MHz Voltage-to-Frequency Converter



PIN Photodiode-to-Frequency Converter



SCALE FACTOR =

1nW/Hz AT 900 NANOMETERS FROM 20nW TO 2mW

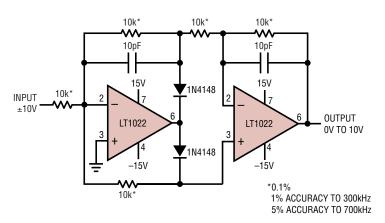


†POLYSTYRENE

* SELECT VALUE FOR 2mW IN = 2MHz OUT

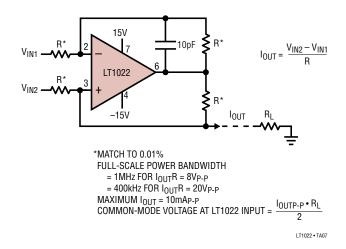
LT1022 • TA05

Wide Bandwidth Absolute Value Circuit

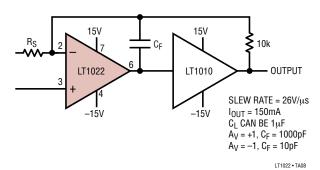


LT1022 • TA06

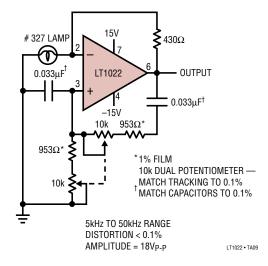
Fast, Differential Input Current Source



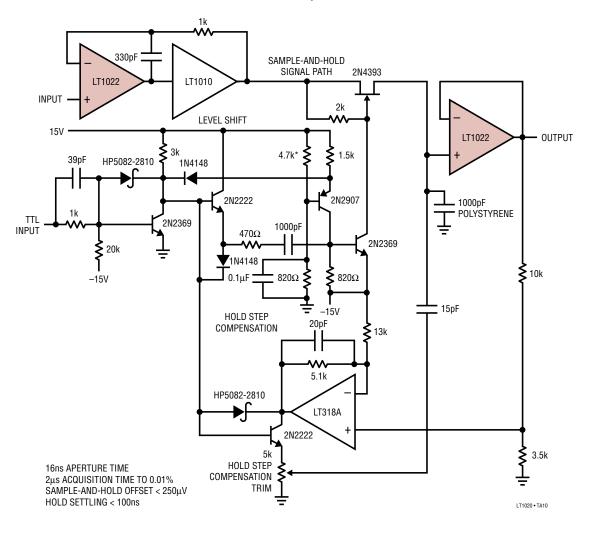
High Output Current Op Amp



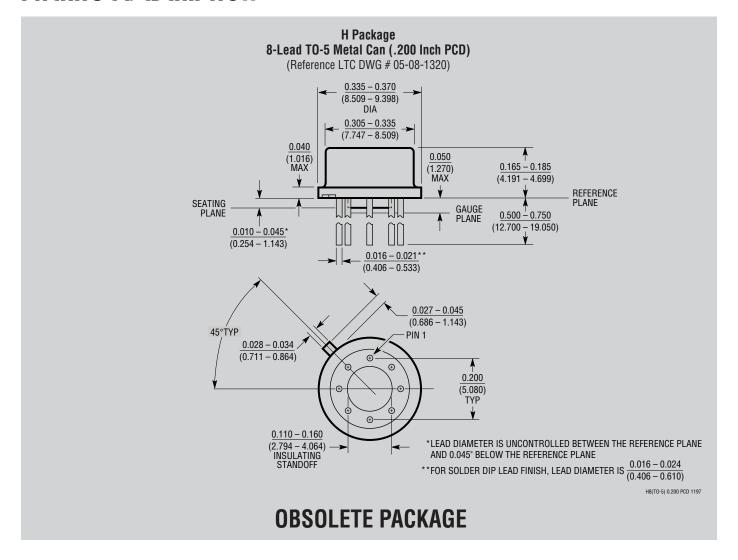
Low Distortion Sine Wave Oscillator



Fast, Precision Sample-And-Hold



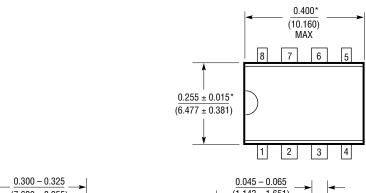
PACKAGE DESCRIPTION

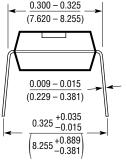


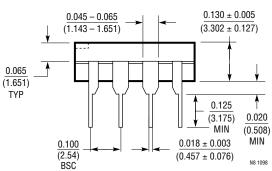
PACKAGE DESCRIPTION

N8 Package 8-Lead PDIP (Narrow .300 Inch)

(Reference LTC DWG # 05-08-1510)







*THESE DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.010 INCH (0.254mm)